



FEATURES

Dimensions are in inch [metric] units.

- 40 pin dual in-line package
- Ideal for electron detection
- 100% internal QE

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C (Per Element)

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	2mm x 5mm		10		mm ²
Responsivity, \mathcal{R}	(see graphs on next page)				A/W
Reverse Breakdown Voltage, V_R	$I_R = 1\mu A$		25		Volts
Capacitance, C	$V_R = 0V$			40	pF
Rise Time	$V_R = 0V$		500		nsec
Shunt Resistance (per element)	$V_f = \pm 10mV$	100			MOhms

THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Ambient ¹	-10° TO 40°C ¹
Nitrogen or Vacuum	-20°C TO 80°C
Maximum Junction Temperature	70°C
Lead soldering temperature ²	260°C

¹Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150nm will be compromised.

²0.080" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.
Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.



1260 Calle Suerte, Camarillo, California 93012
Phone: (805) 499-0335, Fax: (805) 499-8108
Email: sales@optodiode.com, Website: www.optodiode.com

